

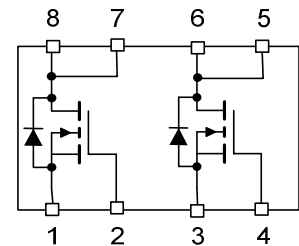
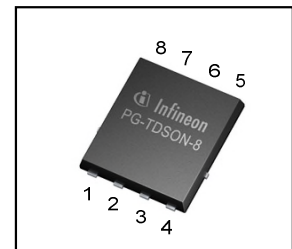
**OptiMOS® Power-Transistor**

**Product Summary**

$V_{DS}$	55	V
$R_{DS(on),max}^{3)}$	65	mΩ
$I_D$	20	A

**Features**

- Dual N-channel Logic Level - Enhancement mode
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested

**PG-TDSON-8**


Type	Package	Marking
IPG20N06S2L-65	PG-TDSON-8	2N06L65

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current one channel active <sup>1)</sup>	$I_D$	$T_C=25\text{ °C}, V_{GS}=10\text{ V}$	20	A
		$T_C=100\text{ °C}, V_{GS}=10\text{ V}$	14	
Pulsed drain current <sup>1)</sup> one channel active	$I_{D,pulse}$	-	80	
Avalanche energy, single pulse <sup>1, 3)</sup>	$E_{AS}$	$I_D=10\text{A}$	40	mJ
Avalanche current, single pulse <sup>3)</sup>	$I_{AS}$	-	15	A
Gate source voltage	$V_{GS}$	-	±20	V
Power dissipation one channel active	$P_{tot}$	$T_C=25\text{ °C}$	43	W
Operating and storage temperature	$T_j, T_{stg}$	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics<sup>1)</sup>**

Thermal resistance, junction - case	$R_{thJC}$	-	-	-	3.5	K/W
SMD version, device on PCB	$R_{thJA}$	minimal footprint	-	100	-	
		6 cm <sup>2</sup> cooling area <sup>2)</sup>	-	60	-	

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	55	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=14\text{ }\mu\text{A}$	1.2	1.6	2.0	
Zero gate voltage drain current <sup>3)</sup>	$I_{DSS}$	$V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.01	1	$\mu\text{A}$
		$V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}^{2)}$	-	1	100	
Gate-source leakage current <sup>3)</sup>	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance <sup>3)</sup>	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=7.5\text{ A}$	-	67	79	m $\Omega$
		$V_{GS}=10\text{ V}, I_D=15\text{ A}$	-	53	65	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>1)</sup>**

Input capacitance <sup>3)</sup>	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	315	410	pF
Output capacitance <sup>3)</sup>	$C_{oss}$		-	90	120	
Reverse transfer capacitance <sup>3)</sup>	$C_{rss}$		-	35	50	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=27.5\text{ V},$ $V_{GS}=10\text{ V}, I_D=20\text{ A},$ $R_G=11\ \Omega$	-	2	-	ns
Rise time	$t_r$		-	3	-	
Turn-off delay time	$t_{d(off)}$		-	10	-	
Fall time	$t_f$		-	7	-	

**Gate Charge Characteristics<sup>1, 3)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=44\text{ V}, I_D=20\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	1.2	1.6	nC
Gate to drain charge	$Q_{gd}$		-	3.5	5.3	
Gate charge total	$Q_g$		-	9.4	12	
Gate plateau voltage	$V_{plateau}$		-	3.9	-	V

**Reverse Diode**

Diode continuous forward current <sup>1)</sup> one channel active	$I_S$	$T_C=25\text{ °C}$	-	-	20	A
Diode pulse current <sup>1)</sup> one channel active	$I_{S,pulse}$		-	-	80	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=15\text{ A},$ $T_j=25\text{ °C}$	-	1.0	1.3	V
Reverse recovery time <sup>1)</sup>	$t_{rr}$	$V_R=27.5\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	30	-	ns
Reverse recovery charge <sup>1, 3)</sup>	$Q_{rr}$		-	28	-	nC

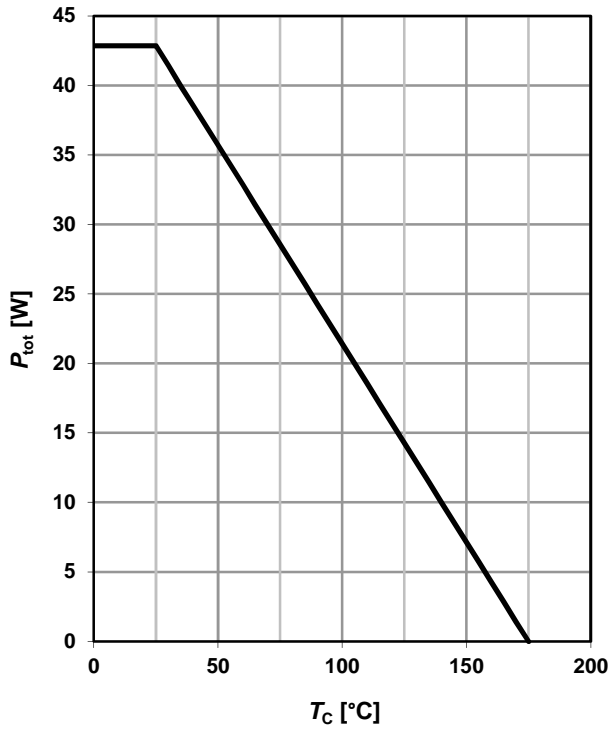
<sup>1)</sup> Specified by design. Not subject to production test.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> Per channel

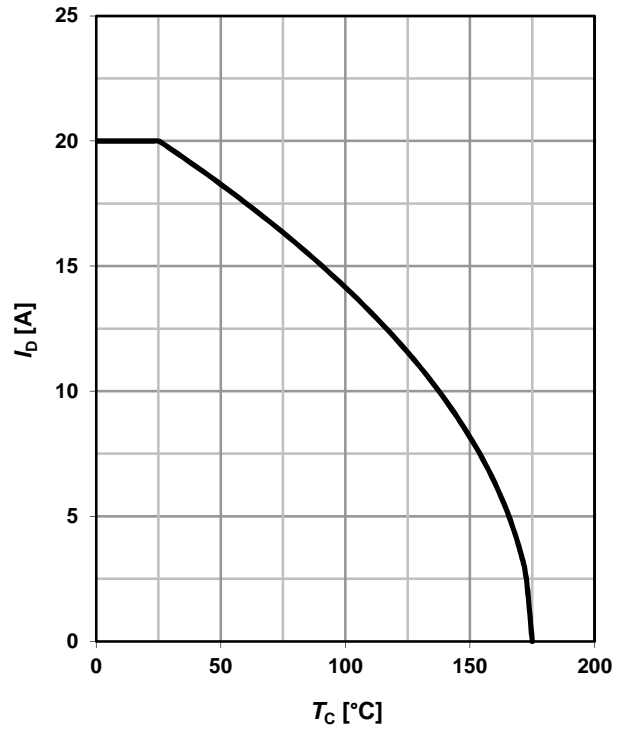
**1 Power dissipation**

$P_{tot} = f(T_C); V_{GS} \geq 6\text{ V};$  one channel active



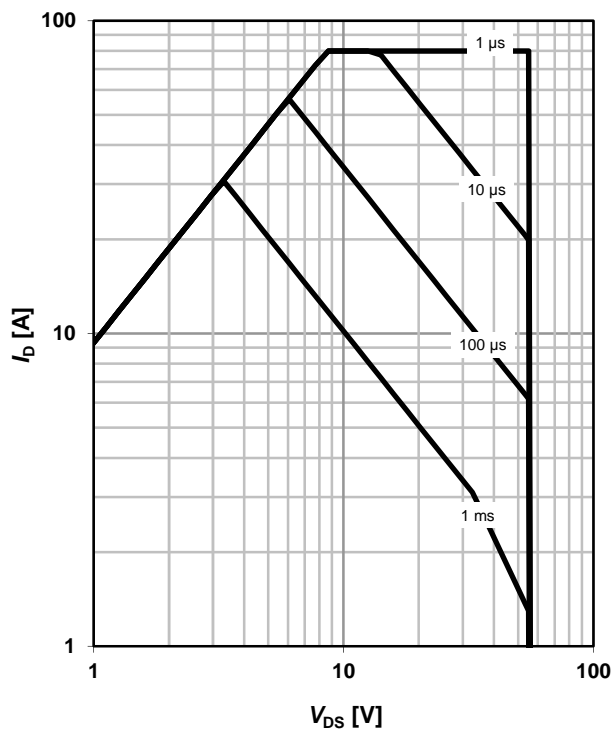
**2 Drain current**

$I_D = f(T_C); V_{GS} \geq 6\text{ V};$  one channel active



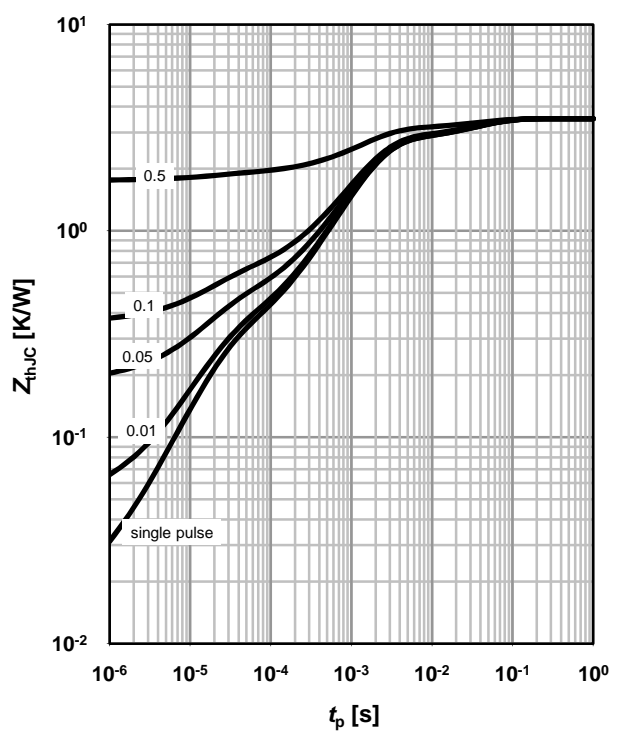
**3 Safe operating area**

$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0;$  one channel active  
parameter:  $t_p$



**4 Max. transient thermal impedance**

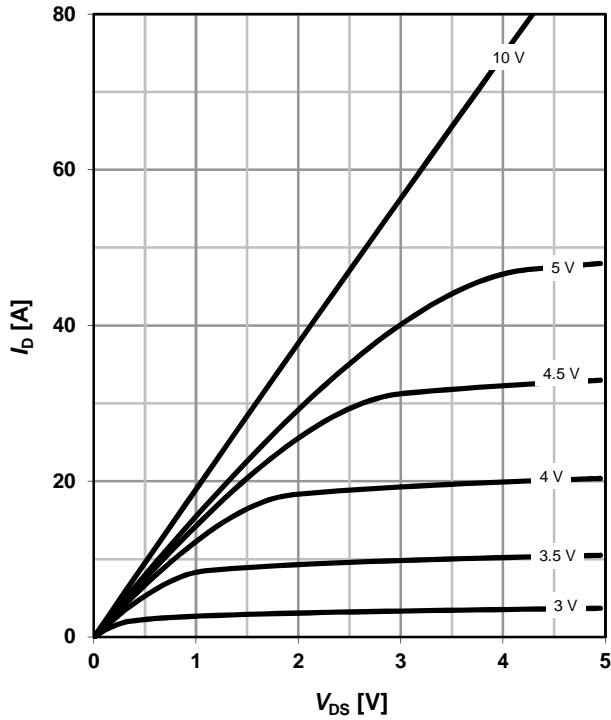
$Z_{thJC} = f(t_p)$   
parameter:  $D = t_p/T$



**5 Typ. output characteristics<sup>3)</sup>**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

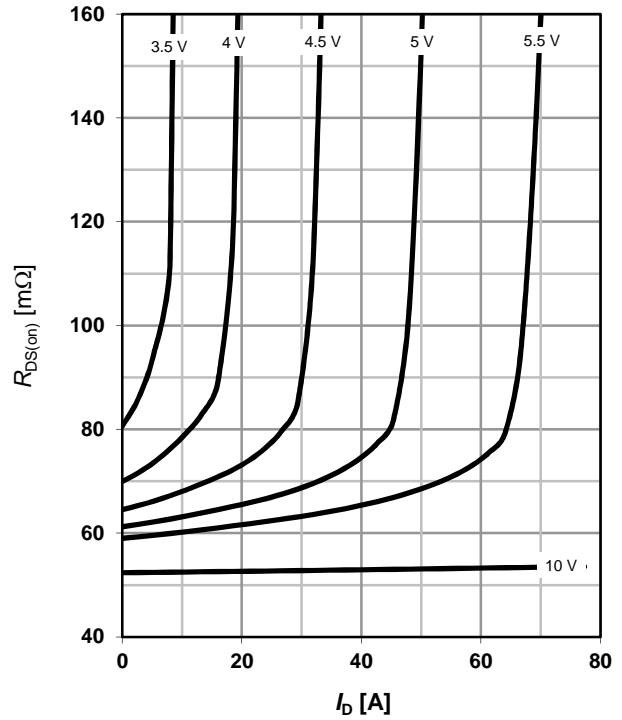
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance<sup>3)</sup>**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

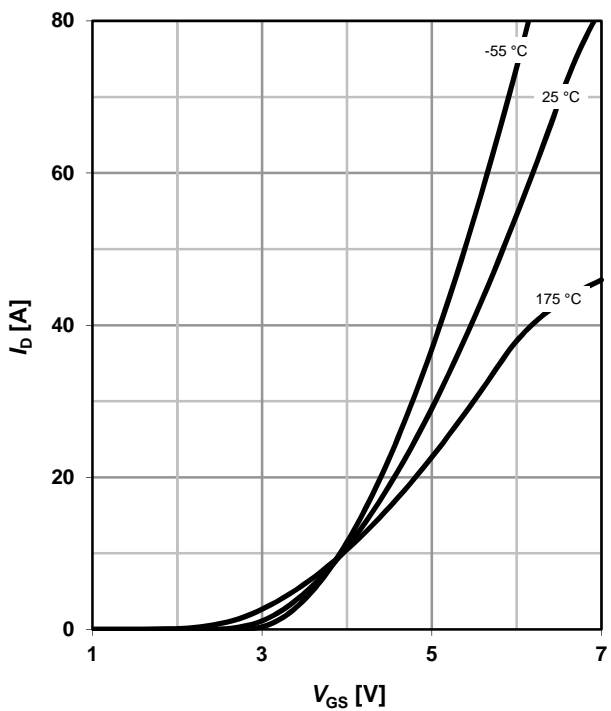
parameter:  $V_{GS}$



**7 Typ. transfer characteristics<sup>3)</sup>**

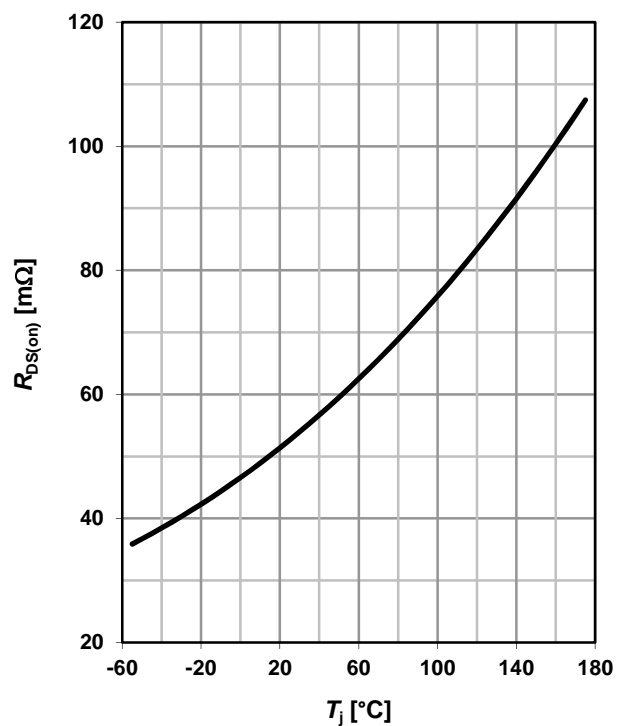
$I_D = f(V_{GS}); V_{DS} = 6V$

parameter:  $T_j$



**8 Typ. drain-source on-state resistance<sup>3)</sup>**

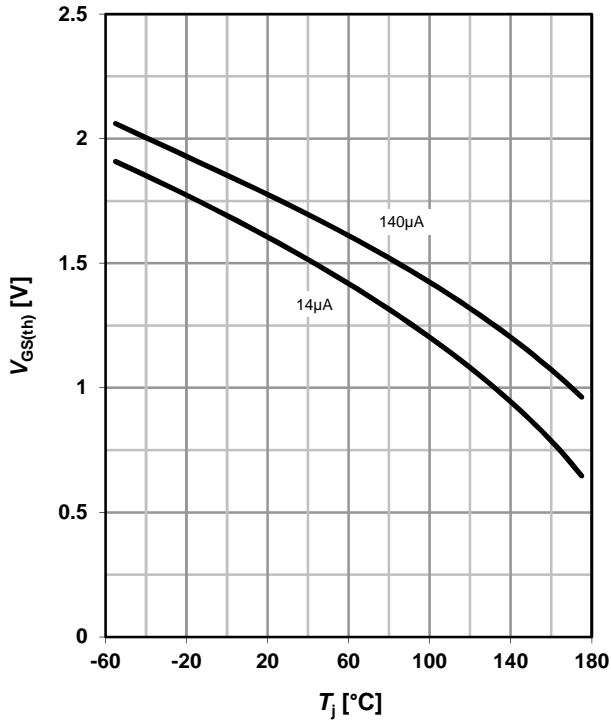
$R_{DS(on)} = f(T_j); I_D = 15\text{ A}; V_{GS} = 10\text{ V}$



**9 Typ. gate threshold voltage**

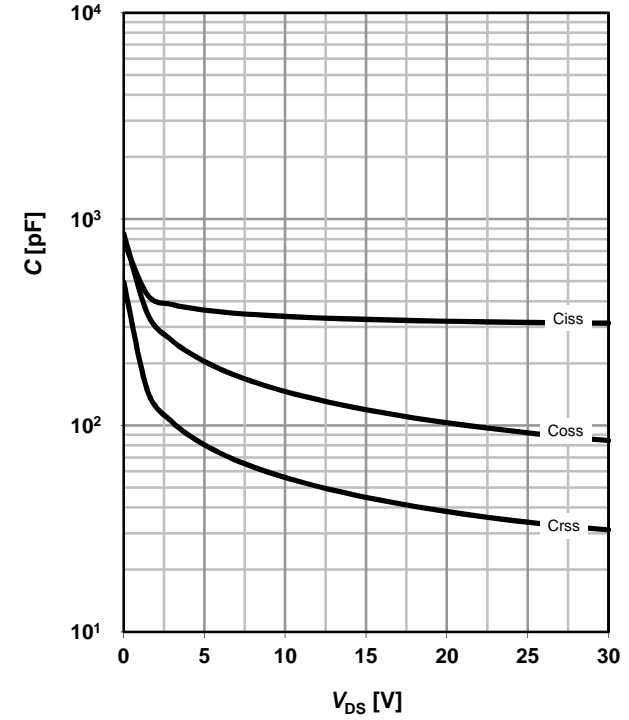
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**10 Typ. Capacitances<sup>3)</sup>**

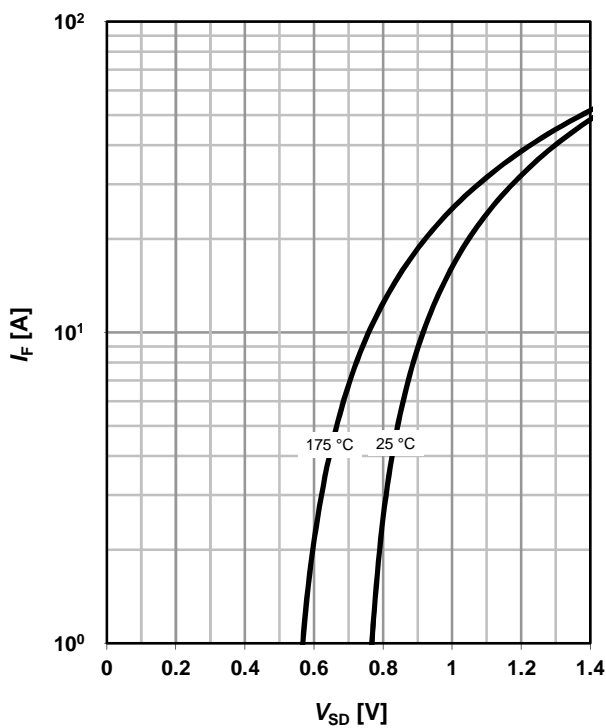
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**11 Typical forward diode characteristics<sup>3)</sup>**

$I_F = f(V_{SD})$

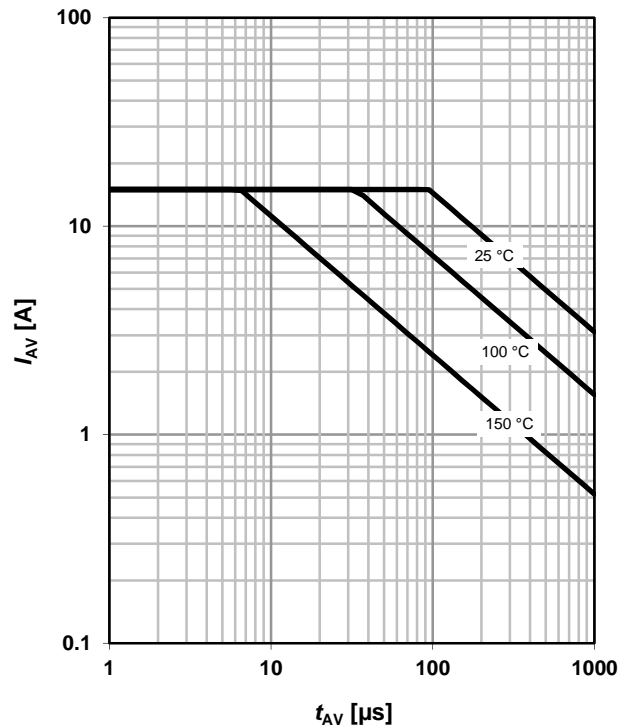
parameter:  $T_j$



**12 Avalanche characteristics<sup>3)</sup>**

$I_{AS} = f(t_{AV})$

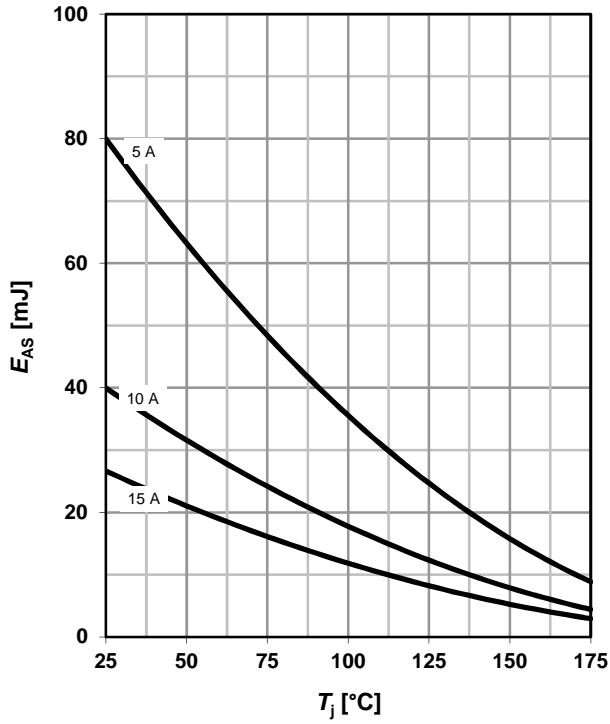
parameter:  $T_{j(start)}$



**13 Avalanche energy<sup>3)</sup>**

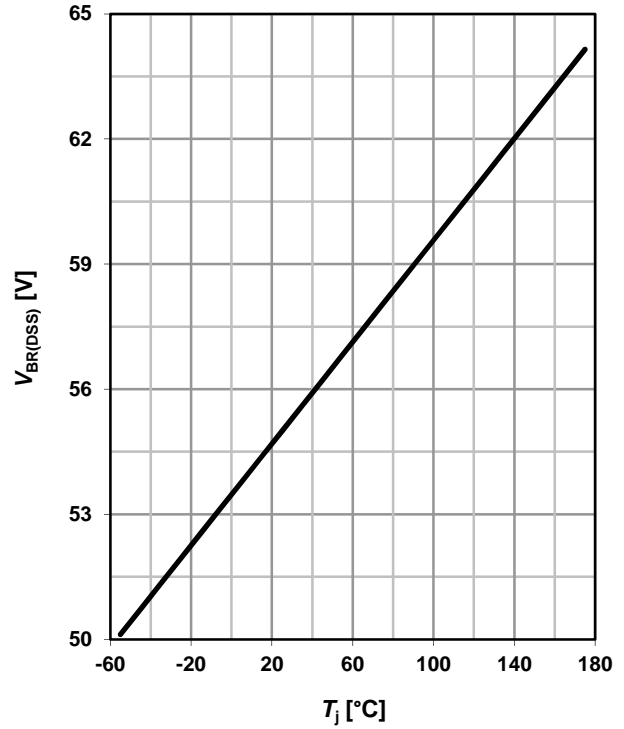
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



**14 Drain-source breakdown voltage**

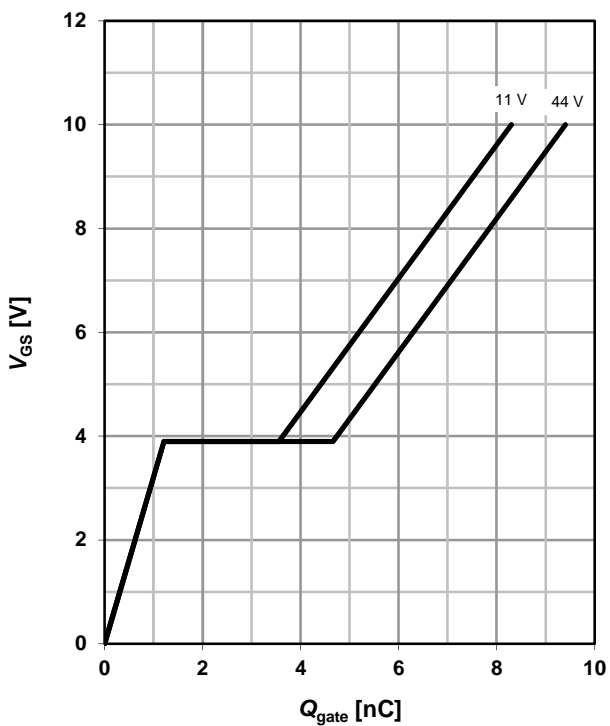
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



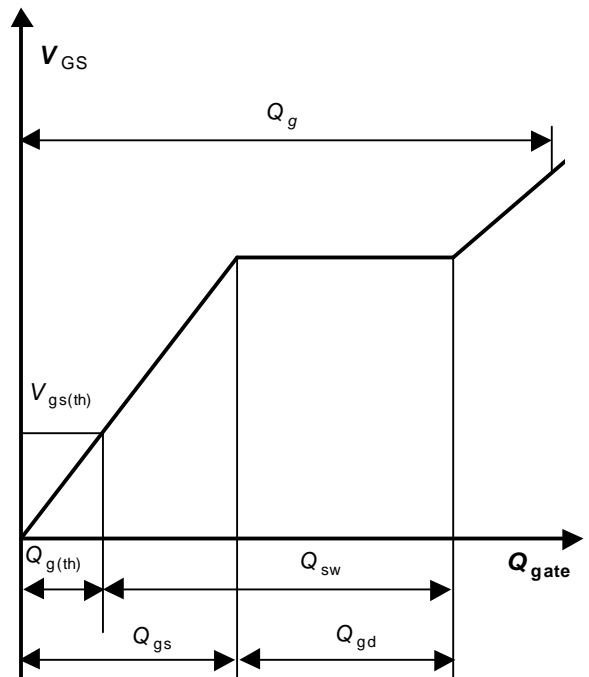
**15 Typ. gate charge<sup>3)</sup>**

$$V_{GS} = f(Q_{gate}); I_D = 20 \text{ A pulsed}$$

parameter:  $V_{DD}$



**16 Gate charge waveforms**



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## Revision History

Version	Date	Changes
Revision 1.0	07.09.2009	Final Data Sheet
Revision 1.01	31.05.2024	Package naming updated